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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-2vqg100

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Introduction

Contents

This user's guide contains information to help designers understand and use Microsemi's ProASIC[®]3 nano devices. Each chapter addresses a specific topic. Most of these chapters apply to other Microsemi device families as well. When a feature or description applies only to a specific device family, this is made clear in the text.

Revision History

The revision history for each chapter is listed at the end of the chapter. Most of these chapters were formerly included in device handbooks. Some were originally application notes or information included in device datasheets.

A "Summary of Changes" table at the end of this user's guide lists the chapters that were changed in each revision of the document, with links to the "List of Changes" sections for those chapters.

Related Information

Refer to the *ProASIC3 nano Low Power Flash FPGAs* datasheet for detailed specifications, timing, and package and pin information.

The website for ProASIC3 nano devices is /www.microsemi.com/soc/products/pa3nano/default.aspx.

FPGA Array Architecture in Low Power Flash Devices



Note: Flash*Freeze technology only applies to IGLOOe devices.

Figure 1-7 • IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)

I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

VersaNet Global Network Distribution

One of the architectural benefits of low power flash architecture is the set of powerful, low-delay VersaNet global networks that can access the VersaTiles, SRAM, and I/O tiles of the device. Each device offers a chip global network with six global lines (except for nano 10 k, 15 k, and 20 k gate devices) that are distributed from the center of the FPGA array. In addition, each device (except the 10 k through 30 k gate device) has four quadrant global networks, each consisting of three quadrant global net resources. These quadrant global networks can only drive a signal inside their own quadrant. Each VersaTile has access to nine global line resources—three quadrant and six chip-wide (main) global networks—and a total of 18 globals are available on the device (3 × 4 regional from each quadrant and 6 global).

Figure 3-1 shows an overview of the VersaNet global network and device architecture for devices 60 k and above. Figure 3-2 and Figure 3-3 on page 34 show simplified VersaNet global networks.

The VersaNet global networks are segmented and consist of spines, global ribs, and global multiplexers (MUXes), as shown in Figure 3-1. The global networks are driven from the global rib at the center of the die or quadrant global networks at the north or south side of the die. The global network uses the MUX trees to access the spine, and the spine uses the clock ribs to access the VersaTile. Access is available to the chip or quadrant global networks and the spines through the global MUXes. Access to the spine using the global MUXes is explained in the "Spine Architecture" section on page 41.

These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local clock networks using spines for up to 252 internal/external clocks or other high-fanout nets in low power flash devices. Optimal usage of these low-skew networks can result in significant improvement in design performance.





Figure 3-1 • Overview of VersaNet Global Network and Device Architecture



Figure 3-6 shows all nine global inputs for the location A connected to the top left quadrant global network via CCC.

Figure 3-6 • Global Inputs

Since each bank can have a different I/O standard, the user should be careful to choose the correct global I/O for the design. There are 54 global pins available to access 18 global networks. For the single-ended and voltage-referenced I/O standards, you can use any of these three available I/Os to access the global network. For differential I/O standards such as LVDS and LVPECL, the I/O macro needs to be placed on (A0, A1), (B0, B1), (C0, C1), or a similar location. The unassigned global I/Os can be used as regular I/Os. Note that pin names starting with GF and GC are associated with the chip global networks, and GA, GB, GD, and GE are used for quadrant global networks. Table 3-2 on page 38 and Table 3-3 on page 39 show the general chip and quadrant global pin names.

I/О Туре	Beginning of I/O Name	Notes
Single-Ended	GAAO/IOuxwByVz	Only one of the I/Os can be directly connected to a
	GAA1/IOuxwByVz	quadrant global at a time
	GAA2/IOuxwByVz	
	GABO/IOuxwByVz	Only one of the I/Os can be directly connected to a
	GAB1/IOuxwByVz	quadrant global at a time.
	GAB2/IOuxwByVz	
	GAC0/IOuxwByVz	Only one of the I/Os can be directly connected to a
	GAC1/IOuxwByVz	quadrant global at a time.
	GAC2/IOuxwByVz	
	GBAO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GBA1/IOuxwByVz	at a time.
	GBA2/IOuxwByVz	
	GBBO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GBB1/IOuxwByVz	at a time.
	GBB2/IOuxwByVz	
	GBC0/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GBC1/IOuxwByVz	at a time.
	GBC2/IOuxwByVz	
	GDAO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GDA1/IOuxwByVz	at a time.
	GDA2/IOuxwByVz	
	GDBO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GDB1/IOuxwByVz	at a time.
	GDB2/IOuxwByVz	
	GDC0/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GDC1/IOuxwByVz	at a time.
	GDC2/IOuxwByVz	
	GEAO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GEA1/IOuxwByVz	at a time.
	GEA2/IOuxwByVz	
	GEBO/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GEB1/IOuxwByVz	at a time.
	GEB2/IOuxwByVz	
	GEC0/IOuxwByVz	Only one of the I/Os can be directly connected to a global
	GEC1/IOuxwByVz	at a time.
	GEC2/IOuxwByVz	

Table 3-3 • Quadrant Global Pin Name

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

Global Resources in Low Power Flash Devices

Using Clock Aggregation

Clock aggregation allows for multi-spine clock domains to be assigned using hardwired connections, without adding any extra skew. A MUX tree, shown in Figure 3-8, provides the necessary flexibility to allow long lines, local resources, or I/Os to access domains of one, two, or four global spines. Signal access to the clock aggregation system is achieved through long-line resources in the central rib in the center of the die, and also through local resources in the north and south ribs, allowing I/Os to feed directly into the clock system. As Figure 3-9 indicates, this access system is contiguous.

There is no break in the middle of the chip for the north and south I/O VersaNet access. This is different from the quadrant clocks located in these ribs, which only reach the middle of the rib.



Figure 3-8 • Spine Selection MUX of Global Tree



Figure 3-9 • Clock Aggregation Tree Architecture

IGLOO and ProASIC3 CCC Locations

In all IGLOO and ProASIC3 devices (except 10 k through 30 k gate devices, which do not contain PLLs), six CCCs are located in the same positions as the IGLOOe and ProASIC3E CCCs. Only one of the CCCs has an integrated PLL and is located in the middle of the west (middle left) side of the device. The other five CCCs are simplified CCCs and are located in the four corners and the middle of the east side of the device (Figure 4-14).



Figure 4-14 • CCC Locations in IGLOO and ProASIC3 Family Devices (except 10 k through 30 k gate devices)

Note: The number and architecture of the banks are different for some devices.

10 k through 30 k gate devices do not support PLL features. In these devices, there are two CCC-GLs at the lower corners (one at the lower right, and one at the lower left). These CCC-GLs do not have programmable delays.

Fusion CCC Locations

Fusion devices have six CCCs: one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-17 and Figure 4-18). The device can have one integrated PLL in the middle of the west side of the device or two integrated PLLs in the middle of the east and west sides of the device (middle right and middle left).



Figure 4-17 • CCC Locations in Fusion Family Devices (AFS090, AFS250, M1AFS250)



Figure 4-18 • CCC Locations in Fusion Family Devices (except AFS090, AFS250, M1AFS250)

Phase Adjustment

The four phases available (0, 90, 180, 270) are phases with respect to VCO (PLL output). The VCO is divided to achieve the user's CCC required output frequency (GLA, YB/GLB, YC/GLC). The division happens after the selection of the VCO phase. The effective phase shift is actually the VCO phase shift divided by the output divider. This is why the visual CCC shows both the actual achievable phase and more importantly the actual delay that is equivalent to the phase shift that can be achieved.

Dynamic PLL Configuration

The CCCs can be configured both statically and dynamically.

In addition to the ports available in the Static CCC, the Dynamic CCC has the dynamic shift register signals that enable dynamic reconfiguration of the CCC. With the Dynamic CCC, the ports CLKB and CLKC are also exposed. All three clocks (CLKA, CLKB, and CLKC) can be configured independently.

The CCC block is fully configurable. The following two sources can act as the CCC configuration bits.

Flash Configuration Bits

The flash configuration bits are the configuration bits associated with programmed flash switches. These bits are used when the CCC is in static configuration mode. Once the device is programmed, these bits cannot be modified. They provide the default operating state of the CCC.

Dynamic Shift Register Outputs

This source does not require core reprogramming and allows core-driven dynamic CCC reconfiguration. When the dynamic register drives the configuration bits, the user-defined core circuit takes full control over SDIN, SDOUT, SCLK, SSHIFT, and SUPDATE. The configuration bits can consequently be dynamically changed through shift and update operations in the serial register interface. Access to the logic core is accomplished via the dynamic bits in the specific tiles assigned to the PLLs.

Figure 4-21 illustrates a simplified block diagram of the MUX architecture in the CCCs.



Note: *For Fusion, bit <88:81> is also needed.

The selection between the flash configuration bits and the bits from the configuration register is made using the MODE signal shown in Figure 4-21. If the MODE signal is logic HIGH, the dynamic shift register configuration bits are selected. There are 81 control bits to configure the different functions of the CCC.

Figure 4-21 • The CCC Configuration MUX Architecture

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

global assignments are not allocated properly. See the "Physical Constraints for Quadrant Clocks" section for information on assigning global signals to the quadrant clock networks.

Promoted global signals will be instantiated with CLKINT macros to drive these signals onto the global network. This is automatically done by Designer when the Auto-Promotion option is selected. If the user wishes to assign the signals to the quadrant globals instead of the default chip globals, this can done by using ChipPlanner, by declaring a physical design constraint (PDC), or by importing a PDC file.

Physical Constraints for Quadrant Clocks

If it is necessary to promote global clocks (CLKBUF, CLKINT, PLL, CLKDLY) to quadrant clocks, the user can define PDCs to execute the promotion. PDCs can be created using PDC commands (pre-compile) or the MultiView Navigator (MVN) interface (post-compile). The advantage of using the PDC flow over the MVN flow is that the Compile stage is able to automatically promote any regular net to a global net before assigning it to a quadrant. There are three options to place a quadrant clock using PDC commands:

- Place a clock core (not hardwired to an I/O) into a quadrant clock location.
- Place a clock core (hardwired to an I/O) into an I/O location (set_io) or an I/O module location (set_location) that drives a quadrant clock location.
- Assign a net driven by a regular net or a clock net to a quadrant clock using the following command:

assign_local_clock -net <net name> -type quadrant <quadrant clock region>
where

<net name> is the name of the net assigned to the local user clock region.

<quadrant clock region> defines which quadrant the net should be assigned to. Quadrant clock regions are defined as UL (upper left), UR (upper right), LL (lower left), and LR (lower right).

Note: If the net is a regular net, the software inserts a CLKINT buffer on the net.

For example:

assign_local_clock -net localReset -type quadrant UR

Keep in mind the following when placing quadrant clocks using MultiView Navigator:

Hardwired I/O–Driven CCCs

• Find the associated clock input port under the Ports tab, and place the input port at one of the Gmn* locations using PinEditor or I/O Attribute Editor, as shown in Figure 4-32.

Figure 4-32 • Port Assignment for a CCC with Hardwired I/O Clock Input



FlashROM in Microsemi's Low Power Flash Devices

Figure 5-12 shows the programming file generator, which enables different STAPL file generation methods. When you select **Program FlashROM** and choose the UFC file, the FlashROM Settings window appears, as shown in Figure 5-13. In this window, you can select the FlashROM page you want to program and the data value for the configured regions. This enables you to use a different page for different programming files.

Figure 5-12 • Programming File Generator

Figure 5-13 • Setting FlashROM during Programming File Generation

The programming hardware and software can load the FlashROM with the appropriate STAPL file. Programming software handles the single STAPL file that contains multiple FlashROM contents for multiple devices, and programs the FlashROM in sequential order (e.g., for device serialization). This feature is supported in the programming software. After programming with the STAPL file, you can run DEVICE_INFO to check the FlashROM content.

7 – I/O Structures in nano Devices

Introduction

Low power flash devices feature a flexible I/O structure, supporting a range of mixed voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V) through bank-selectable voltages. IGLOO[®] and ProASIC3 nano devices support standard I/Os with the addition of Schmitt trigger and hot-swap capability.

Users designing I/O solutions are faced with a number of implementation decisions and configuration choices that can directly impact the efficiency and effectiveness of their final design. The flexible I/O structure, supporting a wide variety of voltages and I/O standards, enables users to meet the growing challenges of their many diverse applications. The Microsemi Libero[®] System-on-Chip (SoC) software provides an easy way to implement I/O that will result in robust I/O design.

This document describes Standard I/O types used for the nano devices in terms of he supported standards. It then explains the individual features and how to implement them in Libero SoC.



Figure 7-1 • I/O Block Logical Representation for Single-Tile Designs (10 k, 15 k, and 20 k devices)



I/O Structures in nano Devices

Table 7-8 • Hot-Swap Level 1

Description	Cold-swap
Power Applied to Device	No
Bus State	-
Card Ground Connection	-
Device Circuitry Connected to Bus Pins	-
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of nano Devices	Compliant

Table 7-9 • Hot-Swap Level 2

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	-
Device Circuitry Connected to Bus Pins Example Application	 In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.



Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307 for details.

Drive Strength

Low power flash devices have up to four programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_8 (slew = low, out_drive = 8 mA).

The maximum available drive strength is 8 mA per I/O. Though no I/O should be forced to source or sink more than 8 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant without adding any extra circuitry. Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

Table 7-17 shows some high-level interfacing examples using low power flash devices.

	Clock		I/O			
Interface	Туре	Frequency	Туре	Signals In	Signals Out	Data I/O
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
TBI	Src Sync	125 MHz	LVTTL	10	10	125 Mbps

Table 7-17 • nano High-Level Interface

Conclusion

IGLOO nano and ProASIC3 nano device support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The nano device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

Related Documents

Application Notes

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

User's Guides

Libero SoC User's Guide http://www.microsemi.com/soc/documents/libero_ug.pdf IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf SmartGen Core Reference Guide http://www.microsemi.com/soc/documents/genguide_ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	Figure 7-2 • I/O Block Logical Representation for Dual-Tile Designs (60 k, 125 k, and 250 k Devices) was revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low (SAR 40698).	160
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	181, 183
June 2011	Figure 7-2 • I/O Block Logical Representation for Dual-Tile Designs (60 k,125 k, and 250 k Devices) was revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	160
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V-tolerant CMOS input buffer and a push-pull output buffer."	166
	The "5 V Input Tolerance" section was revised to state that 5 V input tolerance can be used with LVTTL 3.3 V and LVCMOS 3.3 V configurations. LVCMOS 2.5 V, LVCMOS 1.8 V, LVCMOS 1.5 V, and LVCMOS 1.2 V were removed from the sentence listing supported configurations (SAR 22427).	171

Rules for the DDR I/O Function

- The fanout between an I/O pin (D or Y) and a DDR (DDR_REG or DDR_OUT) macro must be equal to one for the combining to happen on that pin.
- If a DDR_REG macro and a DDR_OUT macro are combined on the same bidirectional I/O, they must share the same clear signal.
- Registers will not be combined in an I/O in the presence of DDR combining on the same I/O.

Using the I/O Buffer Schematic Cell

Libero SoC software includes the ViewDraw schematic entry tool. Using ViewDraw, the user can insert any supported I/O buffer cell in the top-level schematic. Figure 8-5 shows a top-level schematic with different I/O buffer cells. When synthesized, the netlist will contain the same I/O macro.

Figure 8-5 • I/O Buffer Schematic Cell Usage

Input Support for DDR

The basic structure to support a DDR input is shown in Figure 9-2. Three input registers are used to capture incoming data, which is presented to the core on each rising edge of the I/O register clock. Each I/O tile supports DDR inputs.



Figure 9-2 • DDR Input Register Support in Low Power Flash Devices

Output Support for DDR

The basic DDR output structure is shown in Figure 9-1 on page 205. New data is presented to the output every half clock cycle.

Note: DDR macros and I/O registers do not require additional routing. The combiner automatically recognizes the DDR macro and pushes its registers to the I/O register area at the edge of the chip. The routing delay from the I/O registers to the I/O buffers is already taken into account in the DDR macro.



Figure 9-3 • DDR Output Register (SSTL3 Class I)

UJTAG Applications in Microsemi's Low Power Flash Devices



Figure 16-3 • Connectivity Method of UJTAG Macro

UJTAG Operation

There are a few basic functions of the UJTAG macro that users must understand before designing with it. The most important fundamental concept of the UJTAG design is its connection with the TAP Controller state machine.

TAP Controller State Machine

The 16 states of the TAP Controller state machine are shown in Figure 16-4 on page 301. The 1s and 0s, shown adjacent to the state transitions, represent the TMS values that must be present at the time of a rising TCK edge for a state transition to occur. In the states that include the letters "IR," the instruction register operates; in the states that contain the letters "DR," the test data register operates. The TAP Controller receives two control inputs, TMS and TCK, and generates control and clock signals for the rest of the test logic.

On power-up (or the assertion of TRST), the TAP Controller enters the Test-Logic-Reset state. To reset the controller from any other state, TMS must be held HIGH for at least five TCK cycles. After reset, the TAP state changes at the rising edge of TCK, based on the value of TMS.



Figure 17-4 • I/O State as a Function of VCCI and VCC Voltage Levels for IGLOO V5, IGLOO nano V5, IGLOO PLUS V5, ProASIC3L, and ProASIC3 Devices Running at VCC = 1.5 V ± 0.075 V